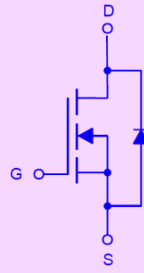


**TO-252**



$V_{DS}$	100V
$I_D$	45A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	17m
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	21.5m
100% UIS Tested	
100% $V_{DS}$ Tested	

Low  $R_{DS(on)}$  & FOM  
Extremely low switching loss  
Excellent stability and uniformity  
Fast switching and soft recovery  
Part no. with suffix "Q" means AEC-Q101 qualified

Power switching application  
Hard switched and high frequency circuits  
Uninterruptible power supply  
DC-DC convertor

( $T_A=25$  unless otherwise noted)

Drain-source Voltage		$V_{DS}$	100	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	7	A
	$T_A=100^\circ C$		4.5	
	$T_C=25^\circ C$		45	
	$T_C=100^\circ C$		28	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	180	A
Avalanche energy <sup>B</sup>		EAS	90	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25^\circ C$	$P_D$	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		73	
	$T_C=100^\circ C$		29	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 +150	$^\circ C$



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Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	R <sub>JA</sub>	40	50	°C/W
Thermal Resistance Junction-to-Case	Steady-State	R <sub>JC</sub>	1.4	1.7	

(Example)

YJD45G10AQ	F1	YJD45G10A	2500	/	25000	13"Reel



( $T_J=25$  unless otherwise noted)

Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
		$V_{DS}=100V, V_{GS}=0V, T_J=150^\circ C$	-	-	100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=22.5A$	-	14	17	m
		$V_{GS}=4.5V, I_D=20A$	-	17	21.5	
Diode Forward Voltage	$V_{SD}$	$I_S=22.5A, V_{GS}=0V$	-	0.9	1.2	V
Maximum Body-Diode Continuous Current	$I_S$		-	-	45	A
Gate resistance	$R_G$	$f=1MHz, \text{Open drain}$	-	1.4	-	
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V, f=1MHz$	-	1165	-	$\mu F$
Output Capacitance	$C_{oss}$		-	265	-	
Reverse Transfer Capacitance	$C_{rss}$		-	8	-	
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=50V, I_D=22.5A$	-	19	-	nC
Gate-Source Charge	$Q_{gs}$		-	6	-	
Gate-Drain Charge	$Q_{gd}$		-	3	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=22.5A, di/dt=100A/\mu s$	-	45	-	nC
Reverse Recovery Time	$t_{rr}$		-	40	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=50V, I_D=22.5A$ $R_{GEN}=2.2$	-	40	-	ns
Turn-on Rise Time	$t_r$		-	12	-	
Turn-off Delay Time	$t_{D(off)}$		-	55	-	
Turn-off fall Time	$t_f$		-	16	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B.  $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\ \Omega, L=0.5mH, I_{AS}=19A$ .

C.  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.

D. The value of  $R_{JA}$  is measured with the device mounted on the minimum recommend pad size, in the still air environment with  $T_A=25^\circ C$ .  
The maximum allowed junction temperature of  $150^\circ C$ . The value in any given application depends on the user's specific board design.

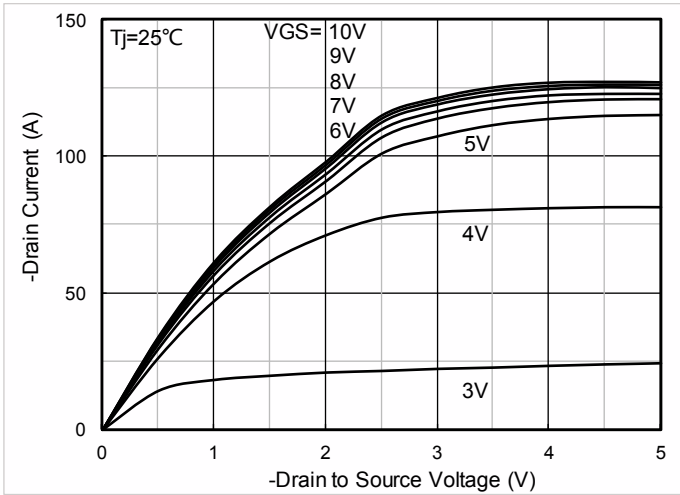


Figure 1. Output Characteristics

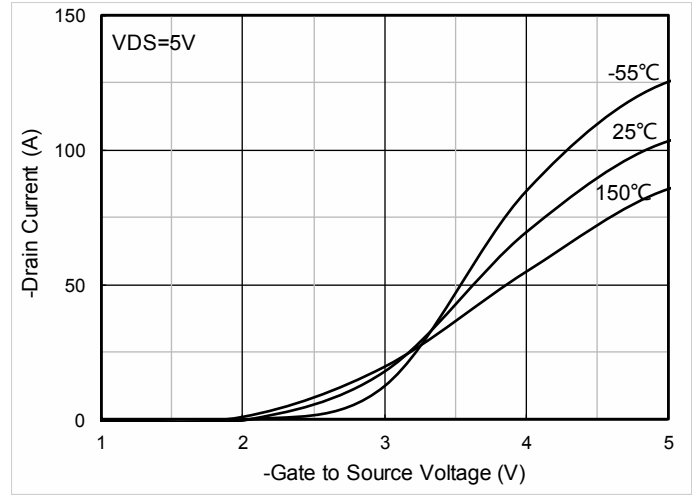


Figure 2. Transfer Characteristics

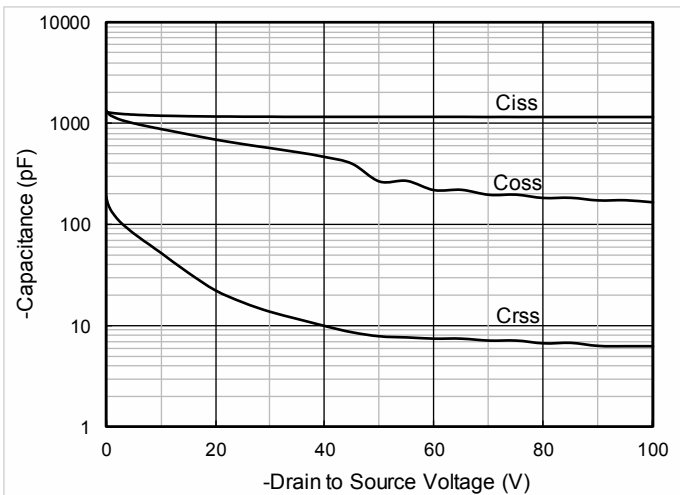


Figure 3. Capacitance Characteristics

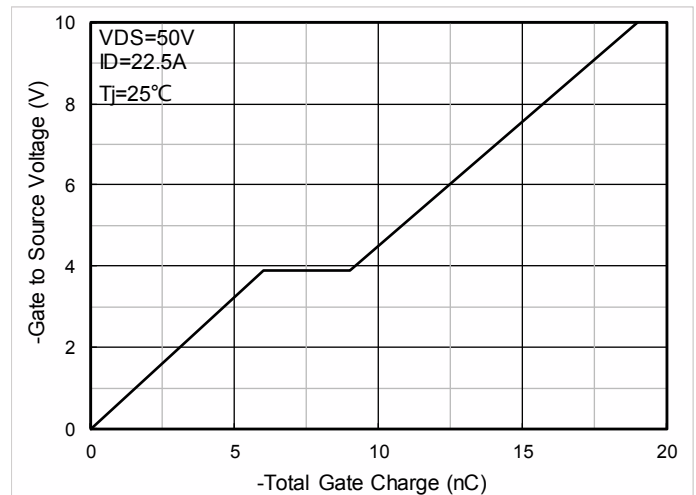


Figure 4. Gate Charge

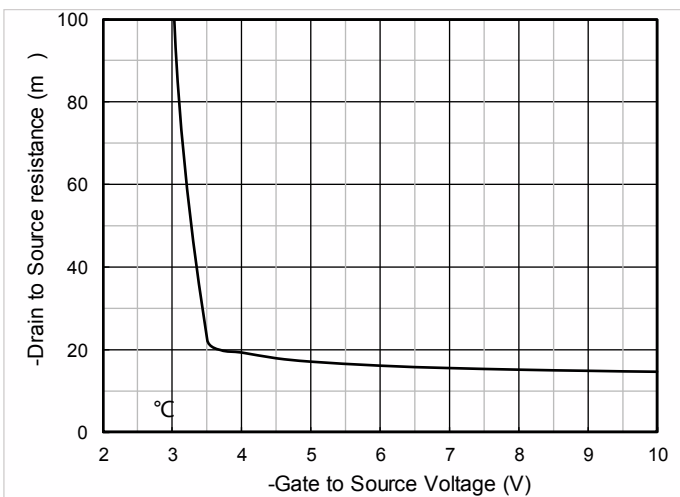


Figure 5. On-Resistance vs Gate to Source Voltage

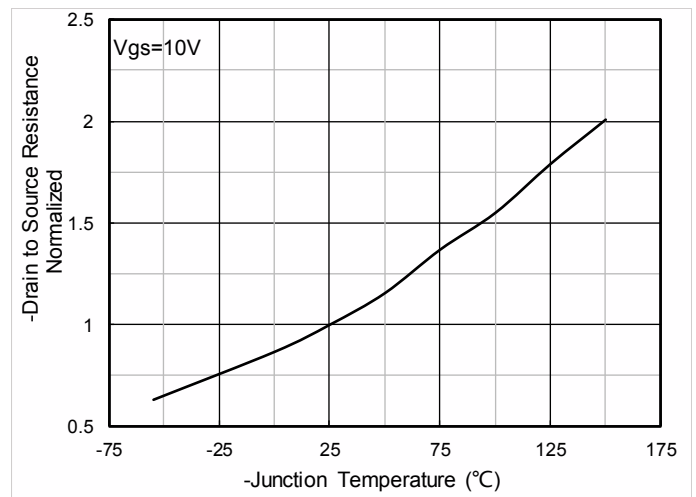


Figure 6. Normalized On-Resistance

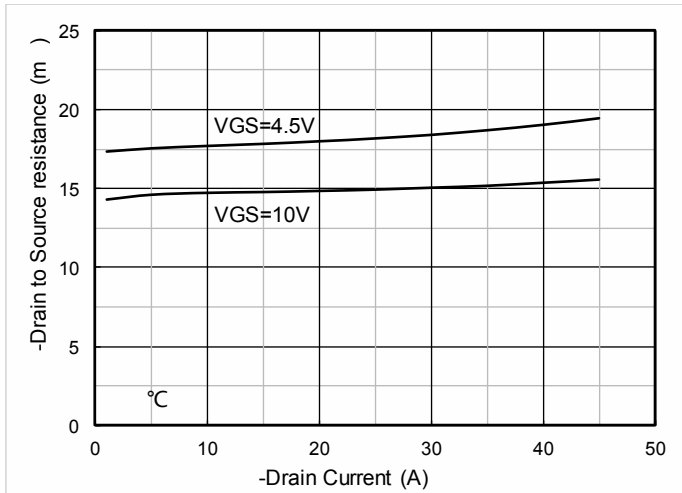


Figure 7.  $R_{DS(on)}$  VS Drain Current

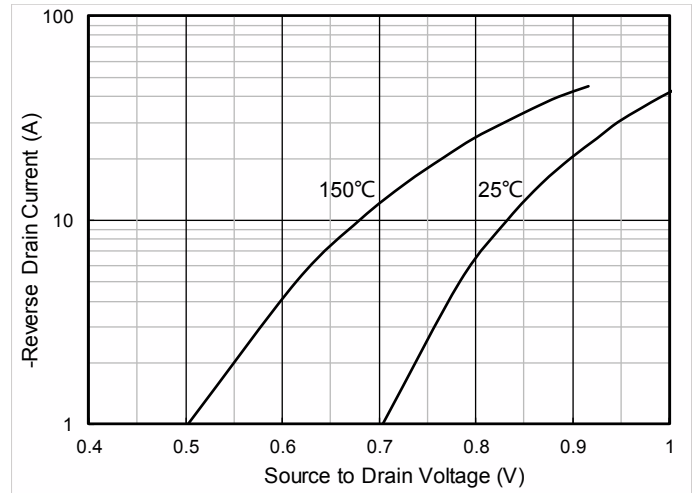


Figure 8.

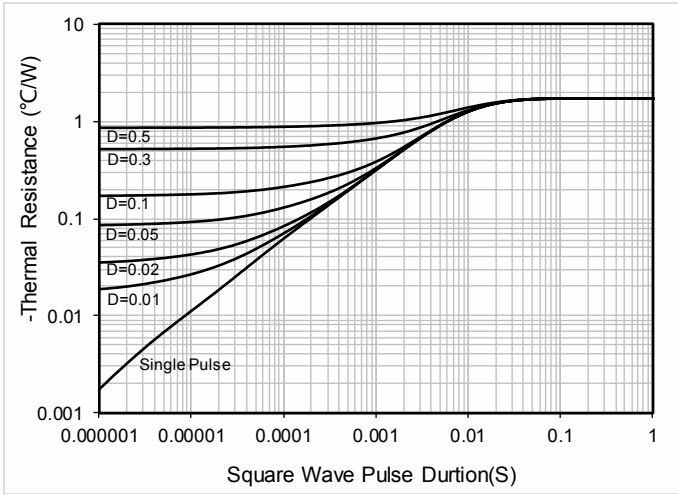


Figure 13. Maximum Transient Thermal Impedance

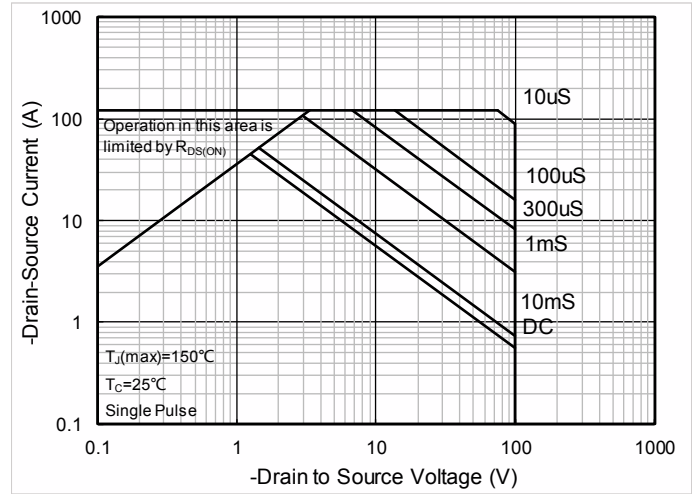


Figure 14. Safe Operation Area

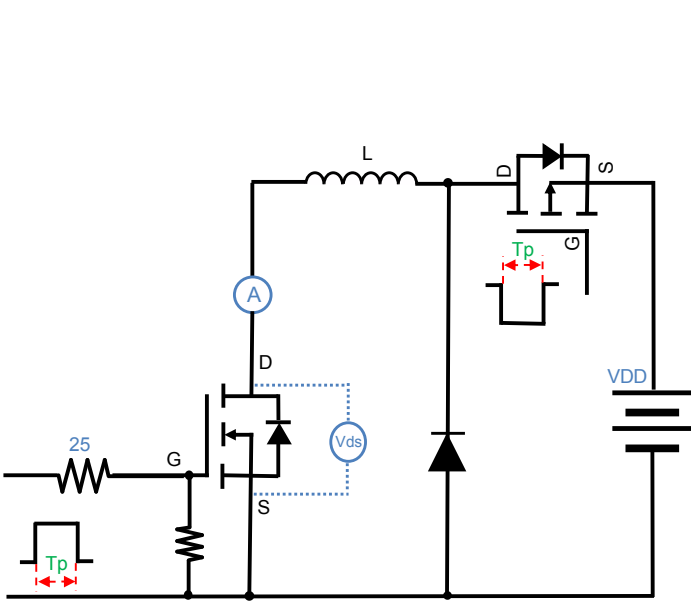
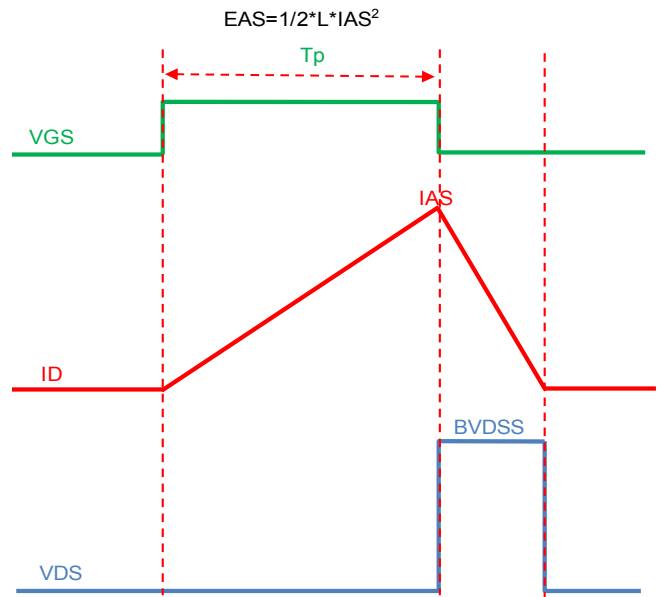


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



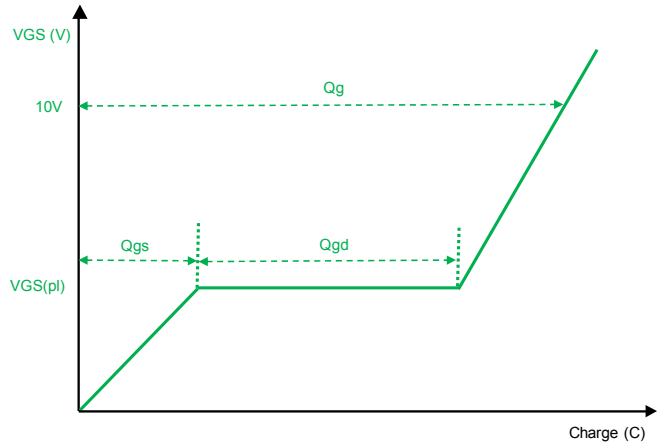
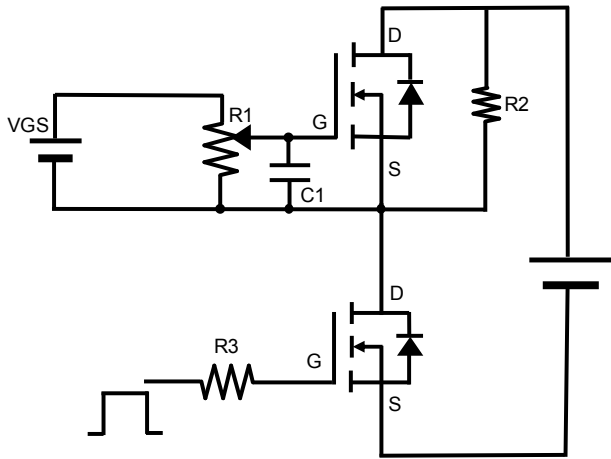


Figure B. Gate Charge Test Circuit & Waveform

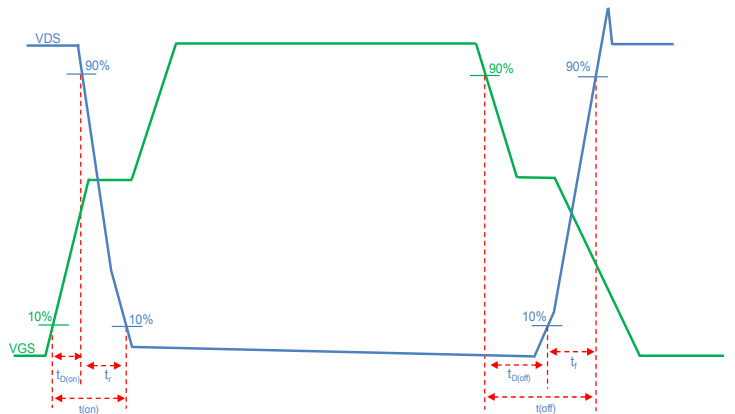
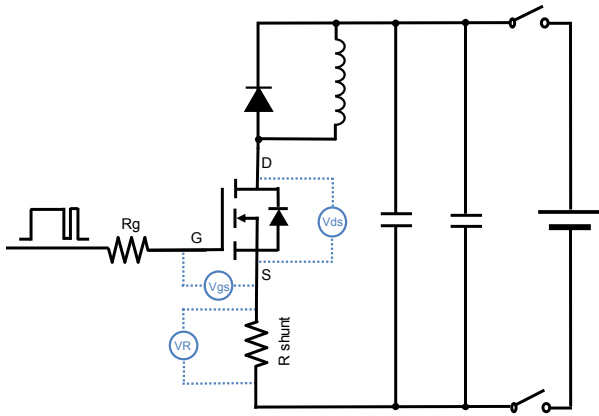


Figure C. Resistive Switching Test Circuit & Waveform

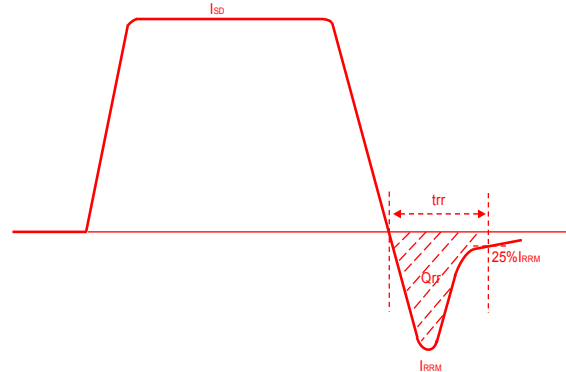
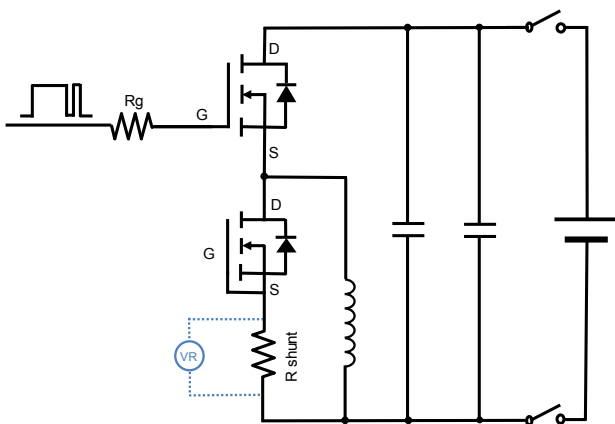
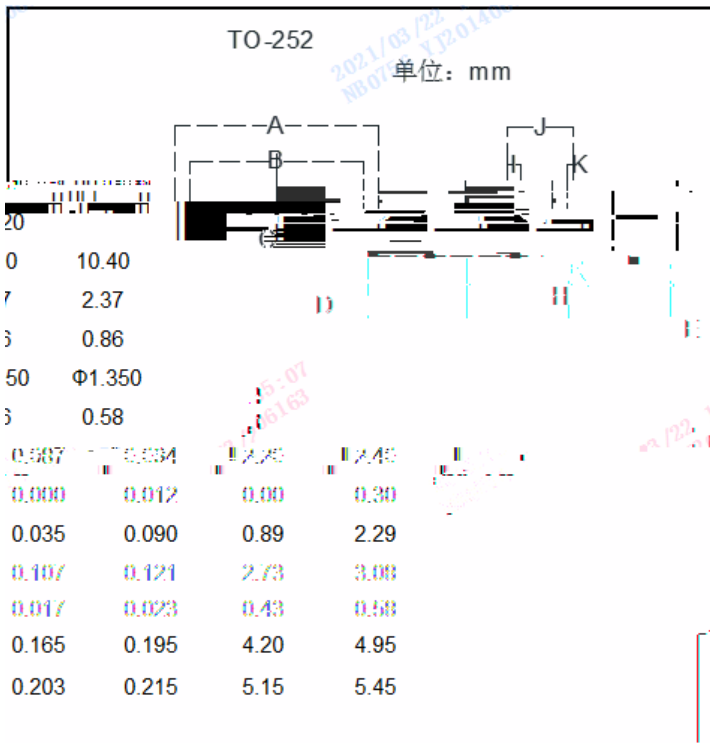
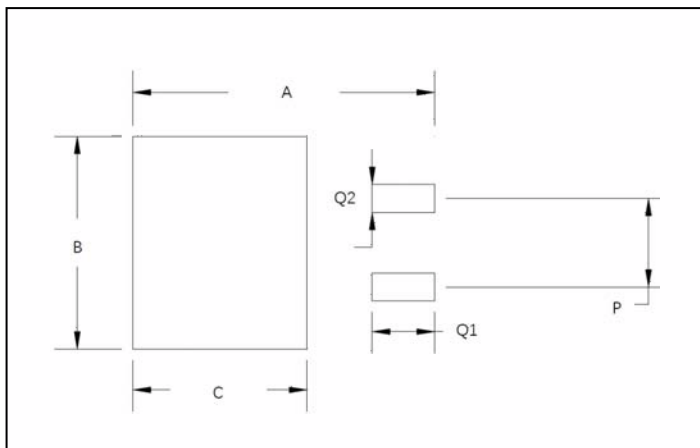


Figure D. Diode Recovery Test Circuit & Waveform



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.256	0.264	6.50	6.70	
B	0.201	0.215	5.10	5.46	
C	0.236	0.244	6.00	6.20	
D	0.236	0.244	6.00	6.20	
E	0.394	0.409	10.0	10.4	
F	0.085	0.093	2.17	2.37	
G	0.026	0.034	0.66	0.86	
H	Φ0.041	Φ0.531	Φ1.0	Φ13.5	
I	0.018	0.023	0.46	0.58	
J					
K					
L					
M					
N					
O					
P					



A	11.4
B	6.74
C	6.23
P	4.56
Q1	2.28
Q2	1.52